UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 6,955,940 B2
DATED : October 18, 2005
INVENTOR(S) : Kristy A. Campbell et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,
Item [56], **References Cited**, FOREIGN PATENT DOCUMENTS,
"WO 97/488032" should read -- WO 97/48032 --.
OTHER PUBLICATIONS,
"Hirose, et al , "Polanty-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As_2S_3 films", Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pps 2767-2772."
should read
-- Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As_2S_3 films", Journal of Applied Physics. Vol. 47. No. 6. Jun. 1976. pps 2767-2772. --.

"Kluge, et al , "Silver photodiffusion in amorphous Ge,Se_{co}", Journal of Non-Crystalline Solids 124 (1990) pps 186-193."
should read
-- Kluge, et al., "Silver photodiffusion in amorphous Ge_xSe_{100-x}", Journal of Non-Crystalline Solids 124 (1990) pps 186-193. --;

"Shimakawa et al., *Photoinduced effects and metastability in amorphous semiconductors and insulators*, 44 Advances n Physics No. 6, 475-588 (Taylor & Francis 1995)."
should read
-- Shimakawa et al., *Photoinduced effects and metastability in amorphous semiconductors and insulators*, 44 Advances in Physics No. 6, 475-588 (Taylor & Francis 1995). --;

"Drusedau, T.P.; Panckow, A.N.; Klabunda, F., The hydrogenated amorphous silicon/ nanodisperse metal (SIMAL) system--Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832."
should read
-- Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/ nanodisperse metal (SIMAL) system--Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832. --;

"Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucal, J., Identation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269."
should read
-- Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269. --;

UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 6,955,940 B2
DATED : October 18, 2005
INVENTOR(S) : Kristy A. Campbell et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page (cont'd),

"Guin, J.-P.; Rouxel, T.; Sangelboeuf, J.-C.; Melscoel, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52."
should read
-- Guin, J.-P.; Rouxel, T.; Sangelboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52. --.

"Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CulnSe2 Crystals, Science 258 (1992) 271-274."
should read
-- Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-temperature, electric field induced creation of stable devices in CuInSe2 crystals, Science 258 (1992) 271-274. --;

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTl chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146."
should read
-- Kotkata, M.F.; Afifi, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTl chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146. --;

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Legarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International Symposium. Sep. 9-13, 1985."
should read
-- Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and EXAFS structural investigation, Transport-structure relations in fast ion and mixed conductors. Proceedings of the 6th Riso International Symposium. Sep. 9-13, 1985. --.

"Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a –Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080."
should read
-- Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in metal/a –Si:H/metal memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080. --.

UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 6,955,940 B2
DATED : October 18, 2005
INVENTOR(S) : Kristy A. Campbell et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page (cont'd),
Item [74], *Attorney, Agent, or Firm*, "Dickstein Shaprio Morin & Oshinsky LLP" should read -- Dickstein Shapiro Morin & Oshinsky LLP --.
Item [57], **ABSTRACT**,
Line 10, "to and HNO_3" should read -- to an HNO_3 --.

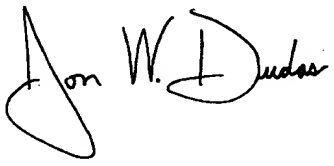
Column 3,
Line 45, "example only, example" should read -- example only, --.

Column 6,
Line 52, "comprises and oxide" should read -- comprises an oxide --.

Column 9,
Line 17, "atomosphere" should read -- atmosphere --.

Signed and Sealed this

Twenty-first Day of March, 2006



JON W. DUDAS
Director of the United States Patent and Trademark Office